

Title (en)  
Current source

Title (de)  
Stromquelle

Title (fr)  
Source de courant

Publication  
**EP 0821460 A3 19980408 (DE)**

Application  
**EP 97111124 A 19970703**

Priority  
CH 181196 A 19960719

Abstract (en)  
[origin: EP0821460A2] The current source has a cascode transistor (T2) whose gate is connected via a first switch (S1) to the drain of an amplifier transistor (T3), whose gate is connected via a second switch (S2) to the drain of a current source transistor (T1). The cascode transistor gate is also connected via a third switch (S3), when a PMOS transistor is used, to an operating voltage (Vdd), or, when an NMOS, to earth. In the on state the first and second switches are closed and the third is open. In the off state the first and second switches are open and the third is closed.

IPC 1-7  
**H02J 1/04**

IPC 8 full level  
**G05F 1/10** (2006.01); **G05F 3/24** (2006.01); **H02J 1/04** (2006.01); **H02J 3/10** (2006.01)

CPC (source: EP)  
**G05F 3/242** (2013.01)

Citation (search report)  
• [A] EP 0637874 A1 19950208 - SIEMENS AG [DE]  
• [A] EP 0722221 A2 19960717 - NEC CORP [JP]  
• [DA] SÄCKINGER ET AL: "a high-swing, high-impedance mos cascode circuit", IEEE JOURNAL OF SOLID STATE CIRCUITS, vol. 25, no. 1, February 1990 (1990-02-01), NEW-YORK, pages 289 - 298, XP000101879

Cited by  
EP1303047A1

Designated contracting state (EPC)  
AT BE CH DE DK ES FI FR GB GR IE IT LI LU MC NL PT SE

DOCDB simple family (publication)  
**EP 0821460 A2 19980128; EP 0821460 A3 19980408; EP 0821460 B1 20020619**; AT E219610 T1 20020715; CZ 223297 A3 19980218; DE 59707548 D1 20020725; PL 183356 B1 20020628; PL 320932 A1 19980202

DOCDB simple family (application)  
**EP 97111124 A 19970703**; AT 97111124 T 19970703; CZ 223297 A 19970715; DE 59707548 T 19970703; PL 32093297 A 19970703